

L Number	Hits	Search Text	DB	Time stamp
1	2067	372/45.ccls.	USPAT	2003/11/26 09:43
2	2067	372/45.ccls.	USPAT	2003/11/26 09:43
3	3606	372/45.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/26 09:43
-	120631	(nitride or nitrate) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/25 13:01
-	2512	(nitride or nitrate) and semiconductor and cladding	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/25 13:02
-	1610	(nitride or nitrate) and semiconductor and cladding and (width or aperture)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/25 13:02
-	253	(nitride or nitrate) and semiconductor and cladding and (current near3 blocking) and (width or aperture)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/25 13:02
-	309	(nitride or nitrate) and semiconductor and cladding and (current near3 blocking)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/25 13:14
-	5452	372/43.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/25 13:14
-	73	372/43.ccls. and ((nitride or nitrate) and cladding)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/25 13:14
-	1	372/54.ccls. and (nitride or nitrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/25 13:15
-	719	(current near3 blocking) and (nitride or nitrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/25 13:15
-	310	(current near3 blocking) and (nitride or nitrate) and cladding	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/25 13:15

L Number	Hits	Search Text	DB	Time stamp
1	2067	372/45.ccls.	USPAT	2003/11/26 09:43
2	2067	372/45.ccls.	USPAT	2003/11/26 09:43
3	3606	372/45.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/26 09:43
-	120631	(nitride or nitrate) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/25 13:01
-	2512	(nitride or nitrate) and semiconductor and cladding	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/25 13:02
-	1610	(nitride or nitrate) and semiconductor and cladding and (width or aperture)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/25 13:02
-	253	(nitride or nitrate) and semiconductor and cladding and (current near3 blocking) and (width or aperture)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/25 13:02
-	309	(nitride or nitrate) and semiconductor and cladding and (current near3 blocking)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/25 13:14
-	5452	372/43.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/25 13:14
-	73	372/43.ccls. and ((nitride or nitrate) and cladding)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/25 13:14
-	1	372/54.ccls. and (nitride or nitrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/25 13:15
-	719	(current near3 blocking) and (nitride or nitrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/25 13:15
-	310	(current near3 blocking) and (nitride or nitrate) and cladding	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/25 13:15